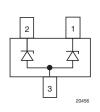


### **Two-Line ESD Protection in SOT-23**





#### **FEATURES**

- Two-line ESD-protection device
- ESD-protection acc. IEC 61000-4-2
   ± 30 kV contact discharge
   ± 30 kV air discharge
- Space saving SOT-23 package
- AEC-Q101 qualified
- e3 Sn
- Material categorization:
   For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>





COMPLIANT
HALOGEN
FREE



#### MARKING (example only)



YYY = type code (see table below) XX = date code

ORDERIN	ORDERING INFORMATION												
	ENV	/IRONMENTAL AN	ID QUALITY CODI	E	PACKAG	ING CODE							
PART NUMBER (EXAMPLE)	AEC-Q101   LEAD (Pb)-FREE TERMINATIONS   IIN   (8 mm TAPF)		1 (8 mm TAPE)		10K PER 13" REEL (8 mm TAPE),	ORDERING CODE (EXAMPLE)							
(2,0 22)	QUALIFIED	STANDARD	GREEN					15K/BOX = MOQ		15K/BOX = MOQ		10K/BOX = MOQ	
GSOT05C-		E		3	-08		GSOT05C-E3-08						
GSOT05C-			G	3	-08		GSOT05C-G3-08						
GSOT05C-	Н	E		3	-08		GSOT05C-HE3-08						
GSOT05C-	Н		G	3	-08		GSOT05C-HG3-08						
GSOT05C-		E		3		-18	GSOT05C-E3-18						
GSOT05C-			G	3		-18	GSOT05C-G3-18						
GSOT05C-	Н	E		3		-18	GSOT05C-HE3-18						
GSOT05C-	Н		G	3		-18	GSOT05C-HG3-18						



PACKA	GE DATA						
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS
GSOT03C	SOT-23	03C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
4301030	301-23	C1G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 O/10 3 at terrimais
GSOT04C	SOT-23	04C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
4301040	301-23	C8G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 O/ TO 3 at terrimas
GSOT05C	SOT-23	05C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
4301030	301-23	C2G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 O/10 3 at terrimas
GSOT08C	SOT-23	08C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
4301000	301-23	C3G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 O/10 3 at terrimas
GSOT12C	SOT-23	12C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
4301120	301-23	C4G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 O/10 3 at terrimas
GSOT15C	SOT-23	15C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
4301130	301-23	C5G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 O/10 3 at terrimas
GSOT24C	SOT-23	24C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
G301240	301-23	C6G	Green	8.1 mg	OL 34 V-0	(according J-STD-020)	200 O/10 3 at terrilliais
GSOT36C	SOT-23	36C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
G301300	JO1-23	C7G	Green	8.1 mg	OL 34 V-0	(according J-STD-020)	200 O/10 3 at terrilliais

ABSOLUTE MAXIMUM RATINGS GSOT03C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	I	30	Α		
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	ІРРМ	30	Α		
Deal of leaves and	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	P <sub>PP</sub>	369	W		
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	т рр	504	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV		
Operating temperature	Junction temperature	TJ	- 55 to + 150	°C		
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT04C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	1	30	А		
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	ІРРМ	30	А		
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	P <sub>PP</sub>	429	W		
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	ГРР	564	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	\/	± 30	kV		
LOD IIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIII	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	± 30	kV		
Operating temperature	Junction temperature	TJ	- 55 to + 150	°C		
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C		



ABSOLUTE MAXIMUM RATINGS GSOT05C					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	<b>I</b>	30	А	
r eak puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	ІРРМ	30	А	
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	P <sub>PP</sub>	480	W	
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		612	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 30	kV	
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV	
Operating temperature	Junction temperature	TJ	- 55 to + 150	°C	
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C	

ABSOLUTE MAXIMUM RATINGS GSOT08C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 µs; single shot	I	18	А		
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	ІРРМ	18	А		
B	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	P <sub>PP</sub>	345	W		
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 µs; single shot	ГРР	400	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 30	kV		
Operating temperature	Junction temperature	$T_J$	- 55 to + 150	°C		
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT12C					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	. I <sub>PPM</sub>	12	А	
r ear puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	ТРРМ	12	Α	
2	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	P <sub>PP</sub>	312	W	
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	ГРР	337	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 30	kV	
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV	
Operating temperature	Junction temperature	T <sub>J</sub>	- 55 to + 150	°C	
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C	



ABSOLUTE MAXIMUM RATINGS GSOT15C					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	l	8	А	
r eak puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p$ = 8/20 $\mu$ s; single shot	· I <sub>РРМ</sub>	8	А	
Ded a lease of	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p$ = 8/20 $\mu$ s; single shot	P <sub>PP</sub>	345	W	
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	ГРР	400	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 30	kV	
ESD IIIIIIdriity	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV	
Operating temperature	Junction temperature	TJ	- 55 to + 150	°C	
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C	

ABSOLUTE MAXIMUM RATINGS GSOT24C					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	lane.	5	А	
reak puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	I <sub>PPM</sub>	5	А	
Deal of land of	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	P <sub>PP</sub>	235	W	
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	ГРР	240	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 30	kV	
L3D illillulity	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV	
Operating temperature	Junction temperature	TJ	- 55 to + 150	°C	
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C	

ABSOLUTE MAXIMUM	RATINGS GSOT36C			
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Dark a large and	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	J	3.5	А
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	20 μs; single shot	3.5	А
Poak pulso powor	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	P <sub>PP</sub>	248	W
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	ГРР	252	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV
ESD initiditity	Air discharge acc. IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 30	kV
Operating temperature	Junction temperature	TJ	- 55 to + 150	°C
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C

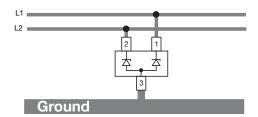
#### **BIAs-MODE** (2-line Bidirectional Asymmetrical protection mode)

With the GSOTxxC two signal- or data-lines (L1, L2) can be protected against voltage transients. With pin 3 connected to ground and pin 1 and pin 2 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified Maximum Reverse Working Voltage (V<sub>RWM</sub>) the protection diode between pin 2 and pin 3 and between pin 1 and pin 3 offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the breakdown voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The Clamping Voltage (V<sub>C</sub>) is defined by the breakdown voltage (V<sub>BR</sub>) level plus the voltage drop at the series impedance (resistance and inductance) of the protection diode.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction through the protection diode. The low Forward Voltage ( $V_F$ ) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the GSOTxxC clamping behavior is Bidirectional and Asymmetrical (BiAs).

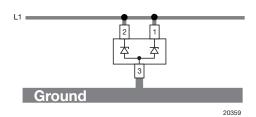




If a higher surge current or peak pulse current (I<sub>PP</sub>) is needed, both protection diodes in the GSOTxxC can also be used in parallel in order to "double" the performance.

#### This offers:

- double surge power = double peak pulse current (2 x I<sub>PPM</sub>)
- half of the line inductance = reduced clamping voltage
- half of the line resistance = reduced clamping voltage
- double line capacitance (2 x C<sub>D</sub>)
- double reverse leakage current (2 x I<sub>R</sub>)



<b>ELECTRICAL CHARACTERISTICS GSOT03C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	2	lines	
Reverse stand-off voltage	at I <sub>R</sub> = 100 μA	$V_{RWM}$	-	-	3.3	V	
Reverse current	at V <sub>R</sub> = 3.3 V	I <sub>R</sub>	-	-	100	μA	
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	4	4.6	-	V	
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	M	-	5.7	7.5	V	
neverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 30 A	V <sub>C</sub>	-	10	12.3	V	
Forward alamaing voltage	at I <sub>PP</sub> = 1 A	W	-	1	1.2	V	
Forward clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 30 A	V <sub>F</sub>	-	4.5	-	V	
Canacitanas	at V <sub>R</sub> = 0 V; f = 1 MHz		-	420	600	pF	
Capacitance	at V <sub>R</sub> = 1.6 V; f = 1 MHz	C <sub>D</sub>	-	260	-	pF	



<b>ELECTRICAL CHARACTERISTICS GSOT04C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	2	lines	
Reverse stand-off voltage	at I <sub>R</sub> = 20 μA	$V_{RWM}$	-	-	4	V	
Reverse current	at V <sub>R</sub> = 4 V	I <sub>R</sub>	-	-	20	μΑ	
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	5	6.1	-	V	
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V	-	7.5	9	V	
heverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 30 A	V <sub>C</sub>	-	11.2	14.3	V	
Forward clamping voltage	at I <sub>PP</sub> = 1 A	V <sub>F</sub>	-	1	1.2	V	
Forward clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 30 A	VF	-	4.5	-	V	
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	- C <sub>D</sub>	-	310	450	pF	
Оараспансе	at V <sub>R</sub> = 2 V; f = 1 MHz	OD	-	200	-	pF	

<b>ELECTRICAL CHARACTERISTICS GSOT05C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	2	lines		
Reverse stand-off voltage	at I <sub>R</sub> = 10 μA	$V_{RWM}$	-	-	5	V		
Reverse current	at V <sub>R</sub> = 5 V	I <sub>R</sub>	-	-	10	μΑ		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	6	6.8	-	V		
Deverse elemening veltage	at I <sub>PP</sub> = 1 A	V	-	7	8.7	V		
Reverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 30 A	V <sub>C</sub>	-	12	16	V		
Forward elemping voltage	at I <sub>PP</sub> = 1 A	V	-	1	1.2	V		
Forward clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 30 A	V <sub>F</sub>	-	4.5	-	V		
Canacitanas	at V <sub>R</sub> = 0 V; f = 1 MHz	- C <sub>D</sub>	-	260	350	pF		
Capacitance	at V <sub>R</sub> = 2.5 V; f = 1 MHz		-	150	-	pF		

<b>ELECTRICAL CHARACTERISTICS GSOT08C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	2	lines		
Reverse stand-off voltage	at I <sub>R</sub> = 5 μA	$V_{RWM}$	-	-	8	V		
Reverse current	at V <sub>R</sub> = 8 V	I <sub>R</sub>	-	-	5	μΑ		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	9	10	-	V		
Poverse elemping veltage	at I <sub>PP</sub> = 1 A	.,	-	10.7	13	V		
Reverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 18 A	V <sub>C</sub>	-	15.2	19.2	V		
Forward elemping voltage	at I <sub>PP</sub> = 1 A	V	-	1	1.2	V		
Forward clamping voltage	ward clamping voltage at I <sub>PP</sub> = I <sub>PPM</sub> = 18 A	V <sub>F</sub>	-	3	-	V		
Canacitanas	at V <sub>R</sub> = 0 V; f = 1 MHz	0	-	160	250	pF		
Capacitance	at V <sub>R</sub> = 4 V; f = 1 MHz	- C <sub>D</sub>	-	80	-	pF		



<b>ELECTRICAL CHARACTERISTICS GSOT12C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	2	lines		
Reverse stand-off voltage	at I <sub>R</sub> = 1 μA	$V_{RWM}$	-	-	12	V		
Reverse current	at V <sub>R</sub> = 12 V	I <sub>R</sub>	-	-	1	μΑ		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	13.5	15	-	V		
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V	-	15.4	18.7	V		
neverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 12 A	V <sub>C</sub>	-	21.2	26	V		
Famuland clamping valtage	at I <sub>PP</sub> = 1 A	V <sub>F</sub>	-	1	1.2	V		
Forward clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 12 A	VF	-	2.2	-	V		
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	- C <sub>D</sub>	-	115	150	pF		
Оараспансе	at V <sub>R</sub> = 6 V; f = 1 MHz		-	50	-	pF		

<b>ELECTRICAL CHARACTERISTICS GSOT15C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	2	lines		
Reverse stand-off voltage	at I <sub>R</sub> = 1 μA	$V_{RWM}$	-	-	15	V		
Reverse current	at V <sub>R</sub> = 15 V	I <sub>R</sub>	-	-	1	μΑ		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	16.5	18	-	V		
Payaraa alamning valtaga	at I <sub>PP</sub> = 1 A	V <sub>C</sub>	-	19.4	23.5	V		
Reverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 8 A	VC	-	24.8	28.8	V		
Forward elemping voltage	at I <sub>PP</sub> = 1 A	V <sub>F</sub>	-	1	1.2	V		
Forward clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 8 A	VF	-	1.8	-	V		
Congoitanos	at V <sub>R</sub> = 0 V; f = 1 MHz	- C <sub>D</sub>	-	90	120	pF		
Capacitance	at V <sub>R</sub> = 7.5 V; f = 1 MHz		-	35	-	pF		

<b>ELECTRICAL CHARACTERISTICS GSOT24C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	2	lines		
Reverse stand-off voltage	at I <sub>R</sub> = 1 μA	$V_{RWM}$	-	-	24	V		
Reverse current	at V <sub>R</sub> = 24 V	I <sub>R</sub>	-	-	1	μΑ		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	27	30	-	V		
Poverse elemning voltage	at I <sub>PP</sub> = 1 A		-	34	41	V		
Reverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 5 A	V <sub>C</sub>	-	41	47	V		
Forward elemping voltage	at I <sub>PP</sub> = 1 A	V <sub>F</sub>	-	1	1.2	V		
Forward clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 5 A	VF	-	1.4	-	V		
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	0	-	65	80	pF		
Сараспансе	at V <sub>R</sub> = 12 V; f = 1 MHz	- C <sub>D</sub>	-	20	-	pF		

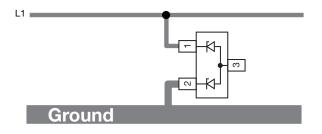


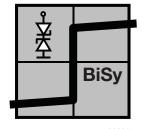
<b>ELECTRICAL CHARACTERISTICS GSOT36C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	2	lines		
Reverse stand-off voltage	at I <sub>R</sub> = 1 μA	$V_{RWM}$	-	-	36	V		
Reverse current	at V <sub>R</sub> = 36 V	I <sub>R</sub>	-	-	1	μΑ		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	39	43	-	V		
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V	-	49	60	V		
heverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 3.5 A	V <sub>C</sub>	-	59	71	V		
Conveyed elemening veltage	at I <sub>PP</sub> = 1 A	\/	-	1	1.2	V		
Forward clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 3.5 A	V <sub>F</sub>	-	1.3	-	V		
Canacitanas	at V <sub>R</sub> = 0 V; f = 1 MHz	- C <sub>D</sub>	-	52	65	pF		
Capacitance	at V <sub>R</sub> = 18 V; f = 1 MHz		=	12	-	pF		

#### **BISy-MODE** (1-line bidirectional symmetrical protection mode)

If a bipolar symmetrical protection device is needed the GSOTxxC can also be used as a single line protection device. Therefore pin 1 has to be connected to the signal- or data-line (L1) and pin 2 to ground (or vice versa). Pin 3 must not be connected. Positive and negative voltage transients will be clamped in the same way. The clamping current through the GSOTxxC passes one diode in forward direction and the other one in reverse direction. The clamping voltage ( $V_C$ ) is defined by the breakthrough voltage ( $V_B$ ) level of one diode plus the forward voltage of the other diode plus the voltage drop at the series impedances (resistances and inductances) of the protection device.

Due to the same clamping levels in positive and negative direction the GSOTxxC voltage clamping behaviour is bidirectional and symmetrical (BiSy).





20361

<b>ELECTRICAL CHARACTERISTICS GSOT03C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines		
Reverse stand-off voltage	at I <sub>R</sub> = 100 μA	$V_{RWM}$	-	-	3.8	V		
Reverse current	at V <sub>R</sub> = 3.8 V	I <sub>R</sub>	-	-	100	μA		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	4.5	5.3	-	V		
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V <sub>C</sub>	-	7	8.4	V		
neverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 30 A	v <sub>C</sub>	-	14	16.8	V		
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	- C <sub>D</sub>	-	210	300	pF		
	at V <sub>R</sub> = 1.6 V; f = 1 MHz		-	190	-	pF		



<b>ELECTRICAL CHARACTERISTICS GSOT04C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines		
Reverse stand-off voltage	at I <sub>R</sub> = 20 μA	$V_{RWM}$	-	-	4.5	V		
Reverse current	at V <sub>R</sub> = 4.5 V	I <sub>R</sub>	-	-	20	μΑ		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	5.5	6.8	-	V		
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V <sub>C</sub>	-	7.5	9	V		
neverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 30 A	v <sub>C</sub>	-	15.7	18.8	V		
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	- C <sub>D</sub>	-	155	225	pF		
	at V <sub>R</sub> = 2 V; f = 1 MHz		-	135	-	pF		

<b>ELECTRICAL CHARACTERISTICS GSOT05C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines		
Reverse stand-off voltage	at I <sub>R</sub> = 10 μA	$V_{RWM}$	-	-	5.5	V		
Reverse current	at V <sub>R</sub> = 5.5 V	I <sub>R</sub>	-	-	10	μA		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	6.5	7.5	-	V		
Doverse elemping voltage	at I <sub>PP</sub> = 1 A	Vc	-	8.1	9.7	V		
Reverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 18 A	VC	-	17	20.4	V		
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	- C <sub>D</sub>	-	130	175	pF		
	at V <sub>R</sub> = 4 V; f = 1 MHz		-	100	-	pF		

<b>ELECTRICAL CHARACTERISTICS GSOT08C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines		
Reverse stand-off voltage	at I <sub>R</sub> = 5 μA	$V_{RWM}$	-	-	8.5	V		
Reverse current	at V <sub>R</sub> = 8.5 V	I <sub>R</sub>	-	-	5	μΑ		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	9.5	10.7	-	V		
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V <sub>C</sub>	-	11.7	14	V		
neverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 18 A	v <sub>C</sub>	-	18.5	22.2	V		
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz		-	80	125	pF		
	at V <sub>R</sub> = 4 V; f = 1 MHz	C <sub>D</sub>	-	60	-	pF		

<b>ELECTRICAL CHARACTERISTICS GSOT12C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines		
Reverse stand-off voltage	at I <sub>R</sub> = 1 μA	$V_{RWM}$	-	-	12.5	V		
Reverse current	at V <sub>R</sub> = 12.5 V	I <sub>R</sub>	-	-	1	μΑ		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	13.5	15.7	-	٧		
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V-	-	16.4	19.7	V		
neverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 12 A	V <sub>C</sub>	-	23.4	28.1	V		
Compositores	at V <sub>R</sub> = 0 V; f = 1 MHz	- C <sub>D</sub>	-	58	75	pF		
Capacitance	at V <sub>R</sub> = 7.5 V; f = 1 MHz		-	36	-	pF		



<b>ELECTRICAL CHARACTERISTICS GSOT15C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines		
Reverse stand-off voltage	at I <sub>R</sub> = 1 μA	$V_{RWM}$	-	-	15.5	V		
Reverse current	at V <sub>R</sub> = 15.5 V	I <sub>R</sub>	-	-	1	μA		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	17	18.7	-	V		
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V-	-	20.4	24.5	V		
neverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 8 A	V <sub>C</sub>	-	26.6	30.6	V		
Constitutes	at V <sub>R</sub> = 0 V; f = 1 MHz	C <sub>D</sub>	-	45	60	pF		
Capacitance	at V <sub>R</sub> = 7.5 V; f = 1 MHz		-	25	-	pF		

<b>ELECTRICAL CHARACTERISTICS GSOT24C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines			
Reverse stand-off voltage	at I <sub>R</sub> = 1 μA	$V_{RWM}$	-	-	24.5	V			
Reverse current	at V <sub>R</sub> = 24.5 V	I <sub>R</sub>	-	-	1	μΑ			
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	27.5	30.7	-	V			
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V <sub>C</sub>	-	34	41	V			
	at I <sub>PP</sub> = I <sub>PPM</sub> = 5 A		-	40	48	V			
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	- C <sub>D</sub>	-	33	40	pF			
	at V <sub>R</sub> = 12 V; f = 1 MHz		-	18	-	pF			

<b>ELECTRICAL CHARACTERISTICS GSOT36C</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines			
Reverse stand-off voltage	at I <sub>R</sub> = 1 μA	$V_{RWM}$	-	-	36.5	V			
Reverse current	at V <sub>R</sub> = 36.5 V	I <sub>R</sub>	-	-	1	μΑ			
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	39.5	43.7	-	V			
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V <sub>C</sub>	-	50	60	V			
	at I <sub>PP</sub> = I <sub>PPM</sub> = 3.5 A		-	60	72	V			
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	C <sub>D</sub>	-	26	33	pF			
	at V <sub>R</sub> = 18 V; f = 1 MHz		-	10	-	pF			



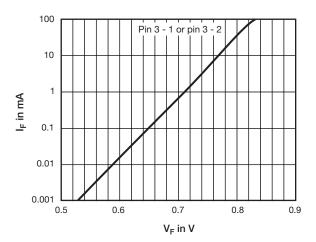


Fig. 1 - Typical Forward Current I<sub>F</sub> vs. Forward Voltage V<sub>F</sub>

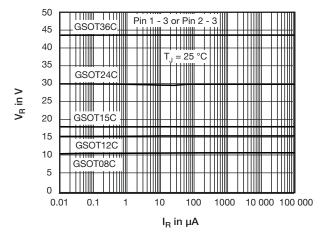


Fig. 2 - Typical Reverse Voltage  $V_{R}$  vs. Reverse Current  $I_{R}$ 

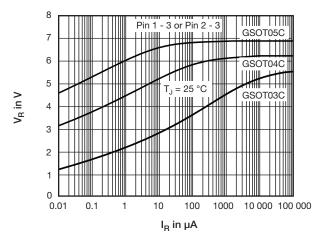
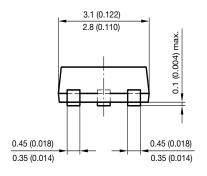
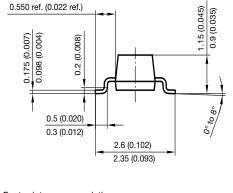


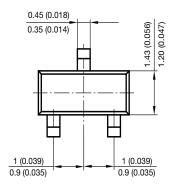
Fig. 3 - Typical Reverse Voltage  $V_{\mbox{\scriptsize R}}$  vs. Reverse Current  $I_{\mbox{\scriptsize R}}$ 

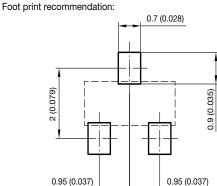
#### PACKAGE DIMENSIONS in millimeters (inches): SOT-23





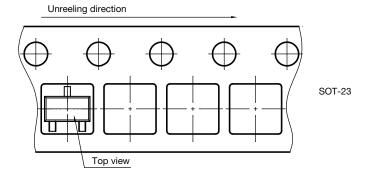
0.550 ref. (0.022 ref.)





Document no.: 6.541-5014.01-4 Rev. 8 - Date: 23.Sept.2009

17418



Orientation in carrier tape S8-V-3929.01-006 (4) 04.02.2010 22607



### **Legal Disclaimer Notice**

Vishay

#### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

## **Material Category Policy**

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000